



PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0029
		Application No.: 10/729,865
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen, et al.
		Filing Date: December 5, 2003
		Group Art Unit: 2824
		Examiner Name: Nguyen, Van Thu T.
Sheet 1 of 2		Date Submitted: December 7, 2005

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
VTN	AA	5,299,166	03-29-1994	Suh et al.		
	AB	6,115,287	09-05-2000	Shimizu et al.		
	AC	6,295,227 B1	09-25-2001	Sakui et al.		
	AD	6,512,694 B2	01-28-2003	Herd		
	AE	6,522,583 B2	02-18-2003	Kanda et al.		
	AF	6,671,204 B2	12-30-2003	Im		
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	AH	6,859,395 B2	02-22-2005	Matsunaga et al.		
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	AK	6,411,548	06-25-2002	Sakui et al.		
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VTN	AM	6,567,287 B2	05-20-2003	Scheuerlein		
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VTN	AN	WO-2002-43067 US	05-2002			
Examiner Signature: <i>Van Thu T. Nguyen</i>				Date Considered	0/6/05	

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<sup>1</sup>Applicant's unique citation designation number (optional).

<sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04.

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<sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

<sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible.

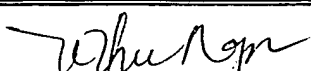
<sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.



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### NON PATENT LITERATURE DOCUMENTS

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VTN	AA	KIM ET AL. "Scaled SONOSFET NAND Flash EEPROM; The NAND Type Flash EEPROM using the Scaled SONOSFET", Transcripts KIEE, Vol. 49C, No. 1, January 2000, pp. 1-7.	Abstract only
I	AB	KOBAYASHI ET AL., "TA 7.2: A 3.3V-Only 16 Mb DINOR Flash Memory," ISSCC95, Session 7, Flash Memory, 1995 IEEE International Solid-State Circuits Conference, pp. 122-123, 349.	
VTN	AC	NAJI, PETER K. ET AL., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM," 2001 IEEE ISSCC, February 6, 2001, Paper 7.6, and corresponding presentation slides (35 pages).	
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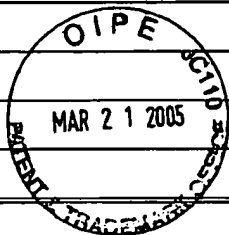






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VTN	AA	4,142,176	02-27-1979	Dozier		
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VTN	AN	JA 62-142363	06-25-1987			
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VTN	AQ	JA-2002-280467	09-27-2002			
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	AS	5,751,012	05-12-1998	Wolstenholme et al.	
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	AW	5,923,587	07-13-1999	Choi	
	AX	5,926,415	07-20-1999	Shin	
	AY	5,940,321	08-17-1999	Takeuchi et al.	
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	BB	6,055,180	04-25-2000	Gudesen et al.	
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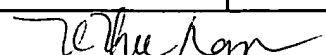
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	BK	6,307,807 B1	10-23-2001	Sakui et al.	
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	BN	6,434,053	08-13-2002	Fujiwara	
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	BQ	6,473,328	10-29-2002	Mercaldi	
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	BS	6,490,194	12-03-2002	Hoenigschmid	
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NTN	BU	6,512,703 B2	01-28-2003	Sakui et al.	

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	CI	6,849,905 B2	02-01-2005	Ilkbahar et al.	
	CJ	6,856,572 B2	02-15-2005	Scheuerlein et al.	
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VTN	CL	US RE. 35,838	07-07-1998	Momodomi et al.	

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NTN	CQ	US-2002/0021587 A1	02-21-2002	Sakui et al.	
	CR	US-2002/0028541 A2	03-07-2002	Lee et al.	
	CS	US-2003/0155582 A1	08-21-2003	Mahajani et al.	
	CT	US-2004/0124415	07-01-2004	Walker et al.	
	CU	US-2004/0124466	07-01-2004	Walker et al.	
	CV	US-2004/0125629 A1	07-01-2004	Scheuerlein et al.	
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	CX	US-6,108,238	08-2000	Nakamura et al.	
	CY	US-6,049,494	04-2000	Sakui et al.	
	CZ	US-5,991,202	11-1999	Derhacopian et al.	
NTN	DA	US-5,812,457	09-1998	Arase	
	DB				
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VTN	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	
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	AF	KIM, BYUNGCEUL, ET AL., "A Scaled SONOS Single-Transistor Memory Cell for a High-Density NOR Structure with Common Source Lines," Journal of the Korean Physical Society, Vol. 41, No. 6, December 2002, pp. 945-948.	
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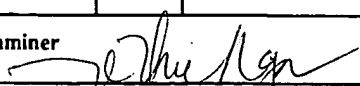
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VTN	AH	US 2001/0055838 A1	27 Dec 2001	Walker et al.		
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		Document	Date	Country	Yes	No
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VTN	AM	0 575 051 A1	22 Dec 1993	Europe		
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